

CGD944C

870 MHz, 25 dB gain power doubler amplifier Rev. 02 — 16 November 2009

Product data sheet

Product profile

1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V (DC), employing Hetero Field Effect Transistor (HFET) GaAs dies.



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- High output capability
- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Rugged construction
- Gold metallization ensures excellent reliability

1.3 Applications

CATV systems operating in the 40 MHz to 870 MHz frequency range

1.4 Quick reference data

Table 1. Quick reference data

	Parameter	Conditions		Тур	Max	Unit
G_p	power gain	f = 870 MHz	24	25	26	dB
I _{tot}	total current	$V_{B} = 24 \text{ V}$	[1] _	450	-	mA

[1] Direct Current (DC)



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Pinning information 2.

Table 2. **Pinning**

	Description		Graphic symbol
1	input		
2, 3	common	1 3 5 7 9	5
5	+V _B		$\frac{1}{2}$ $\frac{9}{2}$
7, 8	common		2378
9	output		sym095
			•

Ordering information 3.

Ordering information Table 3.

	Package			
	Name	Description	Version	
CGD944C	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J	

Limiting values 4.

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Table 4. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Max	Unit
V_{B}	supply voltage		-	30	V
$V_{i(RF)}$	RF input voltage	single tone	-	75	dBmV
		132 channels flat	-	45	dBmV
T _{stg}	storage temperature		-40	+100	°C
T_{mb}	mounting base temperature	Э	-20	+100	°C

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5. Characteristics

Table 5. Characteristics

Bandwidth to 870 MHz; $V_B = 24 \text{ V (DC)}$; $T_{mb} = 35 \text{ }^{\circ}\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions			Тур	Max	Unit
Gp	power gain	f = 870 MHz		24	25	26	dB
SL _{sl}	slope straight line	f = 40 MHz to 870 MHz	[1]	1	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 870 MHz	[2]	-	0.5	-	dB
СТВ	composite triple beat	79 + 53 flat NTSC channels	[3]	-	-68	-66	dBc
		98 flat PAL channels	[4]	-	-66	-	dBc
CSO	composite second-order distortion	79 + 53 flat NTSC channels	[3]	-	-70	-67	dBc
		98 flat PAL channels	[4]	-	-66	-	dBc
Xmod	cross modulation	79 + 53 flat NTSC channels	[3]	-	-66	-58	dB
RL_{in}	input return loss	f = 40 MHz to 80 MHz		20	-	-	dB
		f = 80 MHz to 160 MHz		19	-	-	dB
		f = 160 MHz to 320 MHz		18	-	-	dB
		f = 320 MHz to 640 MHz		18	-	-	dB
		f = 640 MHz to 870 MHz		18	-	-	dB
RL_{out}	output return loss	f = 40 MHz to 80 MHz		20	-	-	dB
		f = 80 MHz to 160 MHz		19	-	-	dB
		f = 160 MHz to 320 MHz		18	-	-	dB
		f = 320 MHz to 640 MHz		18	-	-	dB
		f = 640 MHz to 870 MHz		18	-	-	dB
NF	noise figure	f = 50 MHz		-	3.5	5.0	dB
		f = 870 MHz		-	3.5	5.0	dB
I _{tot}	total current	V _B = 24 V	[5]	-	450	-	mΑ

^[1] G_p at 870 MHz minus G_p at 40 MHz.

^[2] flatness straight line (peak to valley).

^{[3] 79} NTSC channels (5.25 MHz to 547.25 MHz, 48 dBmV output level) + 53 NTSC channels (553.25 MHz to 997.25 MHz, 38 dBmV output level).

^[4] $V_0 = 48 \text{ dBmV}$

^[5] Direct Current (DC)

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6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

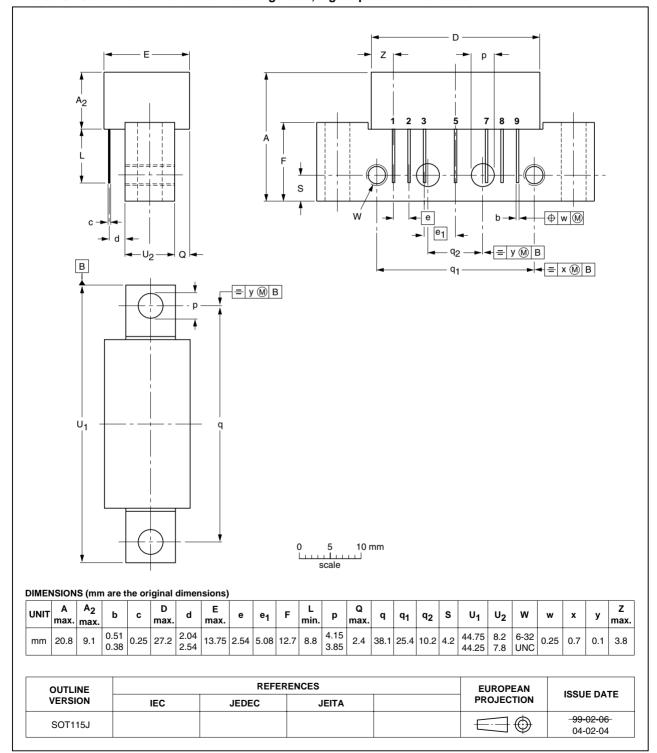


Fig 1. Package outline SOT115J

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Abbreviations

Table 6. **Abbreviations**

Acronym	Description
CATV	Community Antenna TeleVision
DC	Direct Current
GaAs	Gallium-Arsenide
NTSC	National Television Standard Committee
PAL	Phase-Alternation Line
RF	Radio Frequency
UNC	UNified Coarse thread

Revision history

Table 7. **Revision history**

Product data sheet

	Release date	Data sheet status	Change notice	Supersedes
CGD944C_2	20091116	Product data sheet	-	CGD944C_1
Modifications:	 <u>Table 5 on page 3</u>: Correction made <u>Table 5 on page 3</u>: Correction made 			
CGD944C_1	20070606	Product data sheet	-	-

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9.1 Data sheet status

Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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